

STN2580

High voltage fast switching NPN power transistor

Datasheet — production data

Features

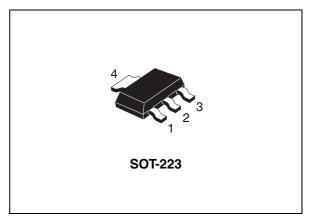
- High voltage capability
- Fast switching speed

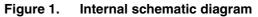
Applications

- Lighting
- Switch mode power supply

Description

This device is a high voltage fast-switching NPN power transistor. It is manufactured using high voltage multi epitaxial planar technology for high switching speeds and medium voltage capability. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA. The device is designed for use in lighting applications and low cost switch-mode power supplies.





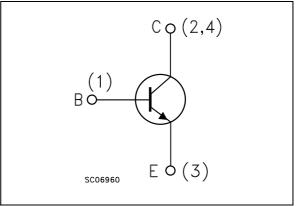


Table 1. Device summary

Order codes	Marking	Package	Packaging	
STN2580 N2580		SOT-223	Tape and reel	

January 2013

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This is information on a product in full production.

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1 Electrical ratings

Table 2.	Absolute max	imum ratings
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Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	800	V
V _{CEO}	Collector-emitter voltage $(I_B = 0)$	400	V
V _{EBO}	Emitter-base voltage (I _C = 0)	9	V
۱ _C	Collector current	1	А
I _{CM}	Collector peak current (t _P < 5 ms)	2	А
I _B	Base current	0.5	А
P _{TOT}	Total dissipation at $T_{amb} = 25 \text{ °C}$	1.6	W
T _{STG}	TG Storage temperature		°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit	
R _{thJA}	Thermal resistance junction-ambient max ⁽¹⁾	78	°C/W	
	2			

1. When mounted on PCB area of 1cm²



2 Electrical characteristics

 T_{case} = 25 °C unless otherwise specified.

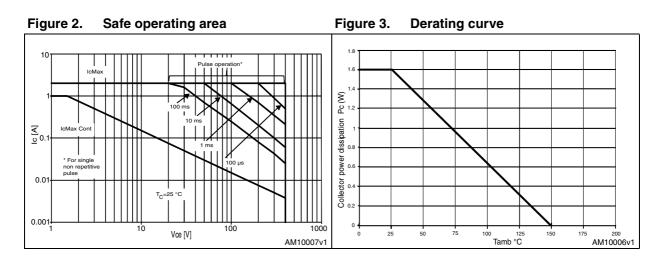
Symbol	Parameter	Test cond	litions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current $(I_E = 0)$	V _{CB} = 800 V				10	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 8 V				100	μA
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage $(I_B = 0)$	I _C = 10 mA		400			v
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E = 100 μA		9			V
h _{FE} ⁽¹⁾	DC current gain	I _C = 250 mA	$V_{CE} = 5 V$	60	100		
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = 1 A	I _B = 0.2 A			1	V
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage $I_C = 1 A$ $I_B = 0.2$		I _B = 0.2 A			1.1	V
	Resistive load						
t _r	Rise time	e V _{CC} =200 V, I _C =0.3 A			140		ns
t _s	Storage time	I _{B1} =20 mA, I _{B2} =-50 mA			4		μs
t _f	Fall time	Τ _p =30 μs			90		ns

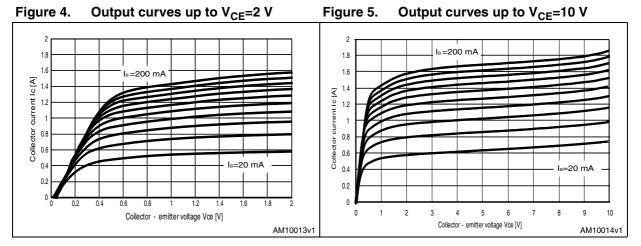
 Table 4.
 Electrical characteristics

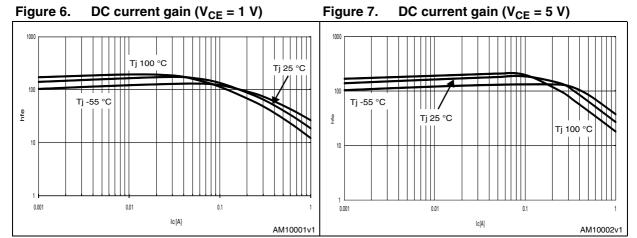
1. Pulse test: pulse duration \leq 300 µs, duty cycle \leq 2%



2.1 Electrical characteristics (curves)







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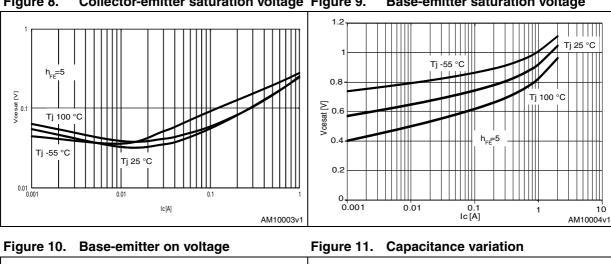


Figure 8. Collector-emitter saturation voltage Figure 9. **Base-emitter saturation voltage**

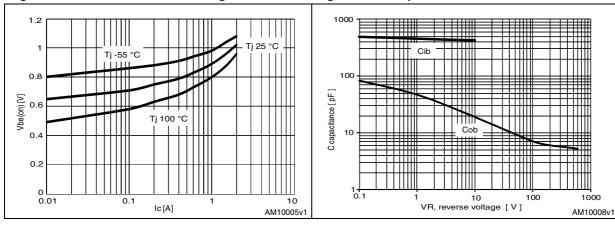
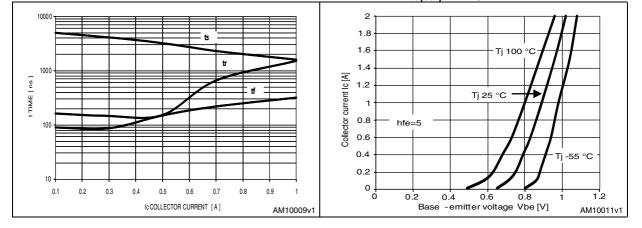




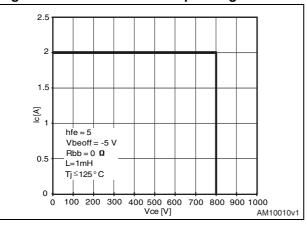
Figure 13. V_{be(sat)} vs. I_C



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3 Test circuit

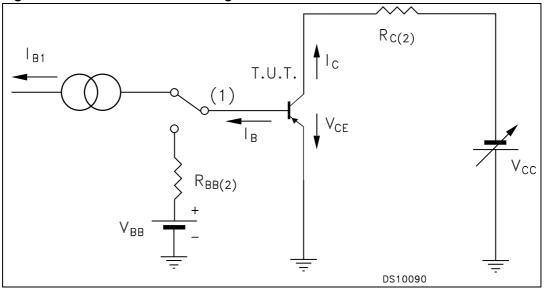


Figure 15. Resistive load switching test circuit

1. Fast electronic switching

2. Non-inductive resistor





4 Package mechanical data

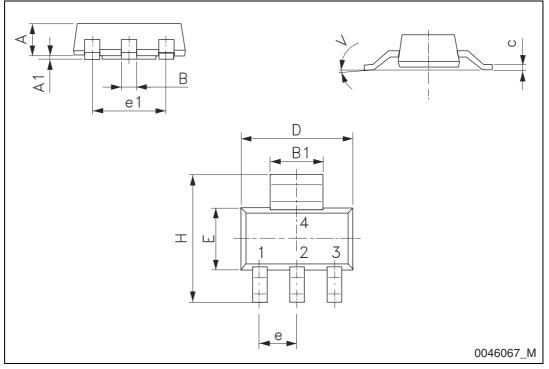
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.



Dim.	mm					
Din.	Min.	Тур.	Max.			
A			1.80			
A1	0.02		0.1			
В	0.60	0.70	0.85			
B1	2.90	3.00	3.15			
С	0.24	0.26	0.35			
D	6.30	6.50	6.70			
e		2.30				
e1		4.60				
E	3.30	3.50	3.70			
Н	6.70	7.00	7.30			
V			10°			

Table 5. SOT-223 mechanical data





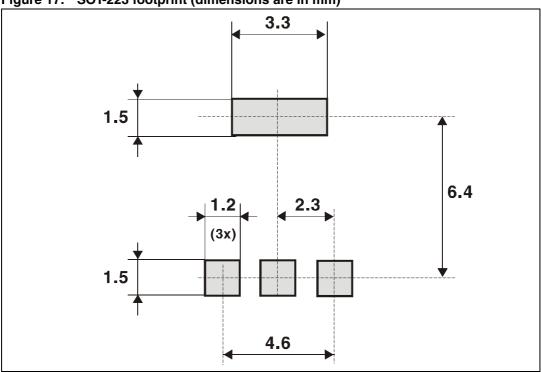


Figure 17. SOT-223 footprint (dimensions are in mm)

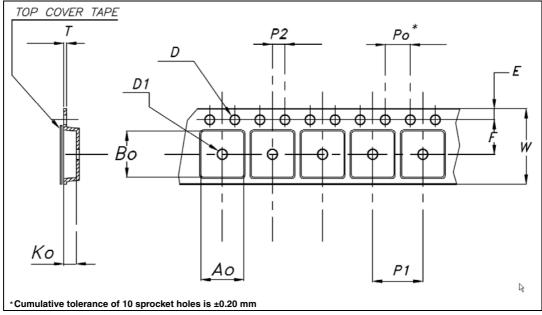


5 Packaging mechanical data

	Таре					
Dim		mm		Dim	mm	
Dim.	n. Dim. Dim. Min. Typ. Max.	Min.	Max.			
A0	6.75	6.85	6.95	А		180
B0	7.30	7.40	7.50	Ν	60	
K0	1.80	1.90	2.00	W1		12.4
F	5.40	5.50	5.60	W2		18.4
Е	1.65	1.75	1.85	W3	11.9	15.4
W	11.7	12	12.3			
P2	1.90	2	2.10	Base qua	antity pcs	1000
P0	3.90	4	4.10	Bulk qua	antity pcs	1000
P1	7.90	8	8.10			
Т	0.25	0.30	0.35			
DØ	1.50	1.55	1.60			
D1¢	1.50	1.60	1.70			

Table 6.	SOT-223 tape and reel mechanical data

Figure 18. Tape for SOT-223





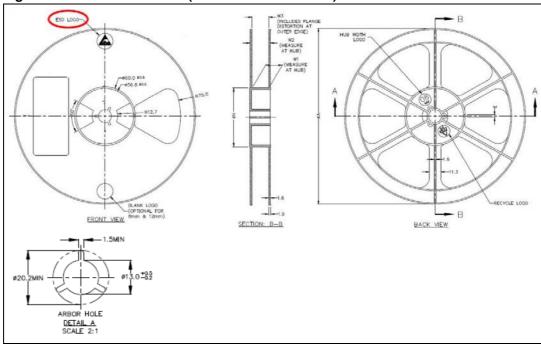


Figure 19. Reel for SOT-223 (dimensions are in mm)



6 Revision history

Table 7.Document revision history

Date	Revision	Changes	
30-Oct-2012	1	Initial release.	
10-Jan-2013	2	Added new section: Packaging mechanical data	



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